

**AMENDMENTS TO THE CLAIMS**

The status of the claims of the present application stands as follows:

Claims 1-18 (**Canceled**)

19. (**Currently Amended**) A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising ~~a first chemical component~~silane and ~~a second chemical component~~arsine, ~~the method comprising the steps of:~~

- a. flowing the exhaust gas through an enclosure defining a chamber having a length and a central axis extending along said length and containing a plurality of substrates spaced from one another along said length and oriented substantially perpendicular to said central axis;
- b. baffling, by said plurality of substrates, the exhaust gas within said chamber so as to increase the residence time of the exhaust gas within said chamber; ~~and~~
- c. causing substantially only the first chemical component of the silane to be thermal chemical vapor deposited onto ones of said plurality of substrates; ~~and~~
- d. subsequent to step c, removing, in a chamber separate from said enclosure, the second chemical componentarsine from the exhaust gas.

20. (**Currently Amended**) A method according to claim 19, ~~further comprising the step of removing the second chemical component from the exhaust gas after performing step c)~~ wherein the step of removing the arsine includes adsorbing the arsine in an adsorber.

21. (**Previously Presented**) A method according to claim 19, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 800°C.

22. **(Previously Presented)** A method according to claim 21, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 1100°C.

23. **(Currently Amended)** A method according to claim 19, wherein ~~the first chemical component is non-toxic and the second chemical component is toxic~~ the step of baffling is performed by forcing the exhaust gas to flow through a plurality of apertures formed in said plurality of substrates.

24. **(Canceled)**

25. **(Currently Amended)** A method according to claim 19, further comprising after step c) the steps of:

- a. removing said at least one of said plurality of substrates from said enclosure;
- b. cleaning said at least one of said plurality of substrates of any film deposited thereon;
- c. installing said at least one of said plurality of substrates in said enclosure; and
- d. again causing only the first chemical components of the silane to be chemical vapor deposited onto said at least one plurality of substrates.

26. **(Currently Amended)** A method of scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a ~~carrier gas~~ silane and a ~~depoant gas~~ arsine, the ~~carrier gas~~ silane comprising a component depositable by thermal chemical vapor deposition, the method comprising ~~the steps of:~~

- a. flowing the exhaust gas through an enclosure defining a chamber having a length and a central axis extending along said length and containing a plurality of substrates spaced from one another along said length and oriented substantially perpendicular to said central axis, said plurality of substrates including a plurality of apertures formed therein;

- b. ~~baffling, by said plurality of substrates, the exhaust gas within said chamber by forcing the exhaust gas to flow substantially only through said plurality of apertures~~ so as to increase the residence time of the exhaust gas within said chamber; and
- c. causing a layer of the component of the ~~earlier gas~~silane to be ~~thermal~~ chemical vapor deposited onto ones of said plurality of substrates; and
- d. ~~removing, in a chamber separate from said enclosure, the dopant gas~~arsine from the exhaust gas after performing step c).

27. **(Currently Amended)** A method according to claim 26, ~~further comprising the step of removing the dopant gas from the exhaust gas after performing step e)~~ wherein the step of removing the arsine includes adsorbing the arsine in an adsorber.
28. **(Previously Presented)** A method according to claim 26, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 800°C.
29. **(Previously Presented)** A method according to claim 28, wherein step c) is performed by heating at least one of (1) said plurality of substrates and (2) said enclosure to at least 1100°C.
30. **(Canceled)**
31. **(Canceled)**
32. **(Previously Presented)** A method according to claim 26, wherein said enclosure contains a plurality of substrates arranged in series with one another along said chamber so as to baffle flow of the exhaust gas.

33. **(Canceled)**

34. **(Canceled)**

35. **(Canceled).**

36. **(Canceled)**

37. **(Previously Presented)** A method according to claim 19, wherein said plurality of substrates are arranged within said chamber so as to cause the exhaust gas to flow along a substantially serpentine path within said chamber.

38. **(Canceled)**